

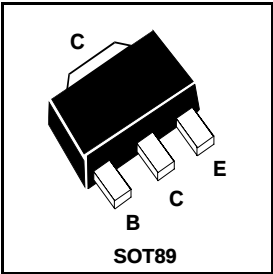
SOT89 NPN SILICON PLANAR
DARLINGTON TRANSISTOR

ISSUE 4 – JANUARY 1996

BCV29

COMPLEMENTARY TYPE – BCV28

PARTMARKING DETAIL – EF



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	10	V
Peak Pulse Current	I_{CM}	800	mA
Continuous Collector Current	I_C	500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40			V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E=10\mu A$
Collector Cut-Off Current	I_{CBO}			100 10	nA μA	$V_{CB}=30V$ $V_{CB}=30V, T_{amb}=150^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1	V	$I_C=100mA, I_B=0.1mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.5	V	$I_C=100mA, I_B=0.1mA^*$
Static Forward Current Transfer Ratio	h_{FE}	4000 10000 20000 4000				$I_C=100\mu A, V_{CE}=1V^{\dagger}$ $I_C=10mA, V_{CE}=5V^*$ $I_C=100mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$
Transition Frequency	f_T		150		MHz	$I_C=50mA, V_{CE}=5V$ $f = 20MHz$
Output Capacitance	C_{obo}		3.5		pF	$V_{CB}=10V, f=1MHz$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical graphs see FMMT38A datasheet $\dagger$ Periodic Sample Test Only.
Spice parameter data is available upon request for this device